

BUZ76

SIPMOS[®] POWER TRANSISTORS

FEATURE

- Nchannel
- Enhancement mode
- Avalanche-rated
- TO-220 envelope
- Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
V_{DS}	Drain-Source Voltage	400	V
I_{DS}	Continuous Drain Current $T_C= 37^{\circ}C$	3	A
I_{DM}	Pulsed Drain Current $T_C= 25^{\circ}C$	12	
I_{AR}	Avalanche Current, Limited by T_{jmax}	3	
E_{AR}	Avalanche Energy, Periodic Limited by T_{jmax}	5	mJ
E_{AS}	Avalanche Energy, Single pulse $I_D = 3 A, V_{DD} = 50 V, R_{GS} = 25 \Omega$ $L = 35 mH, T_j = 25^{\circ}C$	180	
V_{GS}	Gate-Source Voltage	20	V
$R_{DS(on)}$	Drain-Source on Resistance	1.8	Ω
P_T	Power Dissipation at Case Temperature $T_C= 25^{\circ}C$	40	W
t_j	Operating Temperature	-55 to +150	$^{\circ}C$
t_{stg}	Storage Temperature range	-55 to +150	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJC}	Thermal Resistance, chip case	<3.1	K/W
R_{thJA}	Thermal Resistance, chip to ambient	<75	

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
V_{DSS}	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	400	-	-	V
$V_{GS(th)}$	Gate-threshold Voltage	$I_D = 1 mA, V_{GS} = V_{DS}$	2.1	3	4	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400 V, V_{GS} = 0 V$ $T_j = 25 \text{ }^\circ C$	-	0.1	1	μA
		$V_{DS} = 400 V, V_{GS} = 0 V$ $T_j = 125 \text{ }^\circ C$	-	1	100	
I_{GSS}	Gate-Source leakage Current	$V_{GS} = 20 V, V_{DS} = 0 V$	-	10	100	nA
$R_{DS(on)}$	Drain-Source on Resistance	$I_D = 2 A, V_{GS} = 10 V$	-	1.4	1.8	Ω

DYNAMIC CHARACTERISTICS

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
g_{fs}	Transconductance	$V_{DS} > 2 * I_D * R_{DS(on)max}$ $I_D = 2 A$	2.1	3	-	S
C_{ISS}	Input Capacitance	$V_{GS} = 0 V, V_{DS} = 25 V$ $f = 1 MHz$	-	430	650	μF
C_{OSS}	Output Capacitance		-	65	100	
C_{RSS}	Reverse transfer Capacitance		-	25	40	
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30 V, V_{GS} = 10 V$ $I_D = 2.5 A, R_{GS} = 50 \Omega$	-	8	12	ns
t_r	Rise time		-	30	45	
$t_{d(off)}$	Turn-off Delay Time		-	55	75	
t_f	Fall Time		-	30	40	

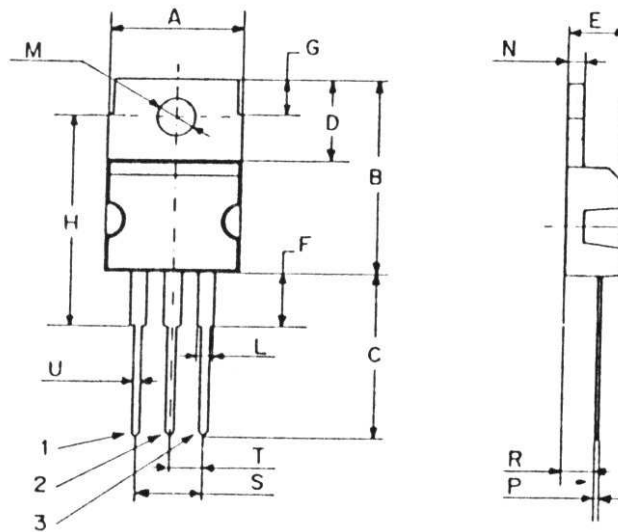
REVERSE DIODE

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
I_S	Inverse Diode Continuous Forward Current.	$T_C = 25 \text{ }^\circ C$	-	-	3	A
I_{SM}	Inverse diode direct current, pulsed.	$T_C = 25 \text{ }^\circ C$	-	-	12	
V_{SD}	Inverse Diode Forward voltage	$V_{GS} = 0 V, I_F = 6 A$	-	1	1.4	V
T_{rr}	Reverse Recovery Time	$V_R = 100 V, I_F = I_S$ $di_F/dt = 100 A/\mu s$	-	300	-	ns
Q_{rr}	Reverse Recovery Charge		-	2.5	-	μC

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Gate
Pin 2 :	Drain
Pin 3 :	Source

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